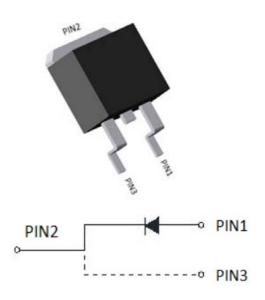




Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (135°C)}	22A
Qc	62nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_o=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106520BXQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	٧	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	٧	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	650
Continuous forward current @ T _c =25°C			48
Continuous forward current @ T _c =135°C	l _F	А	22
Continuous forward current @ T _c =140°C			20
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160
Power Dissipation@ T₀=25°C	Б	W	144
Power Dissipation@ T₀=110°C	- P _{TOT}		62
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	128
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

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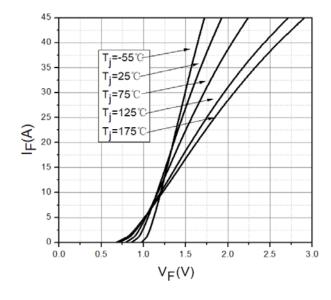
■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Forward voltage drap	V _F	V	I _F =20A, T _j =25°C	1.35	1.55		
Forward voltage drop		V	I _F =20A, T _j =175°C	1.75	-		
Povorco logicado gurrent	I _R μA	V _R =650V, T _j =25°C	1	25			
Reverse leakage current		μΑ	V _R =650V, T _j =175°C	5	-		
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C, $QC=\int_0^{VR}C(V)dV$	62	-		
	C pF	С			V _R =0V, f=1MHZ	1157	-
Total capacitance			C pF	V _R =200V, f=1MHZ	115.6	-	
		V _R =400V, f=1MHZ	107	-			
Capacitance Stored Energy	Ec	μJ	V _R =400V	7.8	-		

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	1.04

■Typical Characteristics



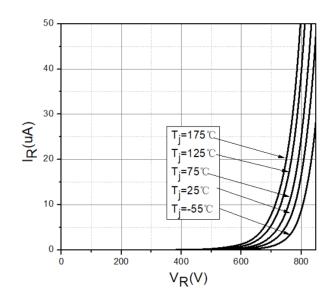
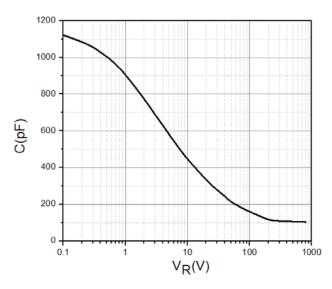


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristic





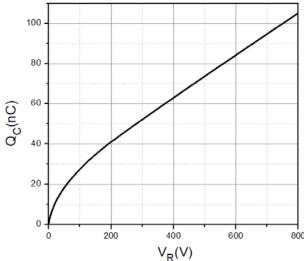
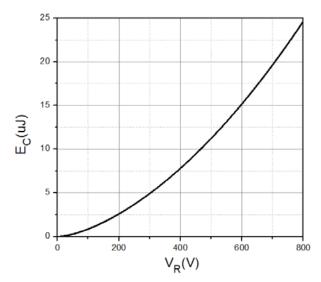


Figure 3. Capacitance vs. Reverse Voltage

Figure 4. Total Capacitance Charge vs. Reverse Voltage



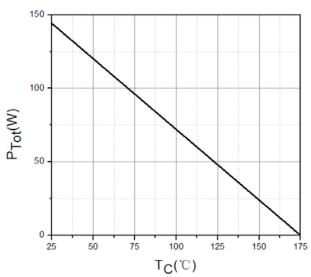
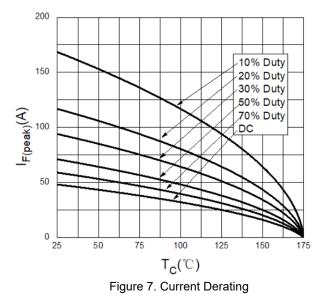


Figure 5. Capacitance Stored Energy

Figure 6. Power Derating



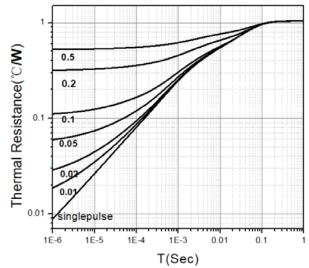
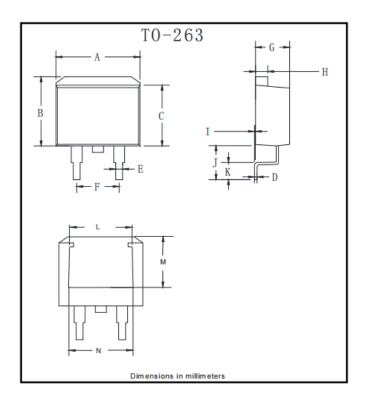


Figure 8. Transient Thermal Impedance





■Outline Dimensions



TO-263			
Dim	Min	Max	
Α	9.5	11.5	
В	9.7	10.5	
С	8.4	9.0	
D	0.28	0.64	
E	0.68	0.94	
F	4.55	5.6	
G	4.04	5.10	
Н	1.14	1.4	
I	0	0.2	
J	4.9	6.05	
K	1.79	2.79	
L	7.3	7.9	
M	6.2	6.8	
N	7.6	8.2	



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